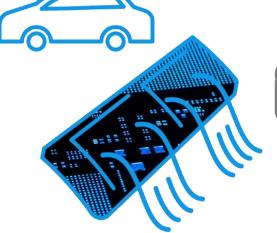
Automotive HVAC

Solution Proposal by Toshiba



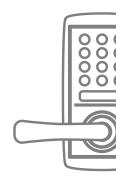






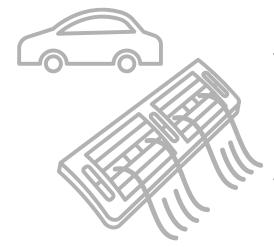




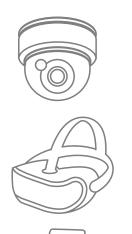








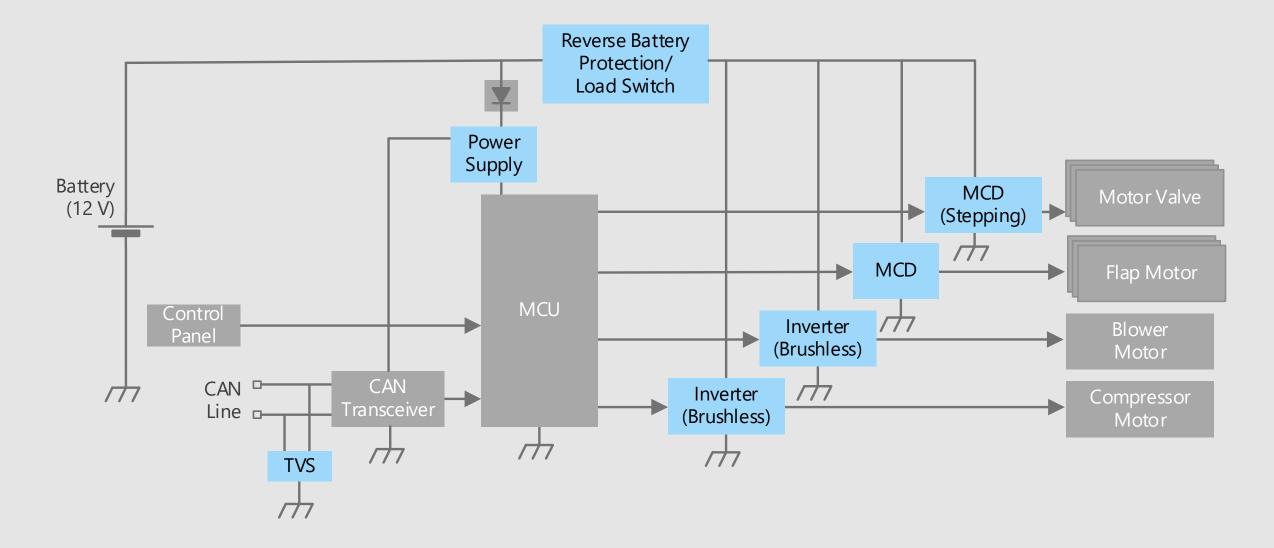
Toshiba Electronic Devices & Storage Corporation provides comprehensive device solutions to customers developing new products by applying its thorough understanding of the systems acquired through the analysis of basic product designs.



Block Diagram

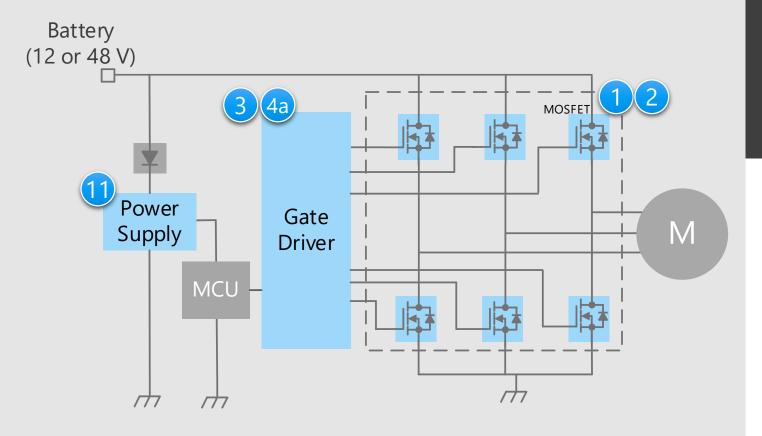
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HVAC Overall block diagram



HVAC Detail of brushless DC motor drive

Brushless DC motor drive circuit



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

Low on-resistance contributes low power consumption of the system

U-MOS Series 40 V N-ch MOSFET U-MOS Series 100 V N-ch MOSFET

 Gate driver with built-in protection and diagnosis functions
 Gate driver (for motor)

- Noise reduction using sinusoidal current wave
Brushless DC motor pre driver for blower

- Voltage regulator with low current consumption Power supply IC (for MCU)

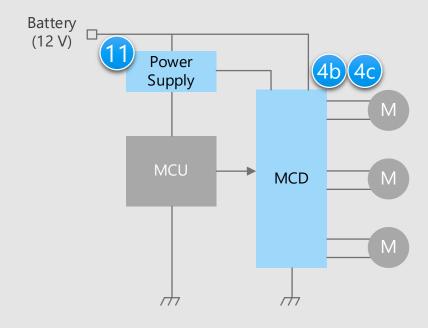
1

2



HVAC Detail of brushed DC motor drive

Brushed DC motor drive circuit



Criteria for device selection

- -The number of parts can be reduced by using the motor control IC with the built-in output driver.
- -A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- -Suitable for driving a small brush DC motor
- Brushed DC motor driver for damper 4b 4c



-Voltage regulator with low current consumption

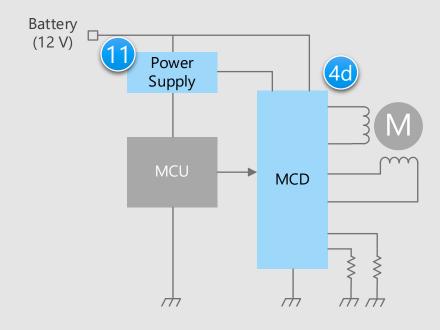
Power supply IC (for MCU)



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

HVAC Detail of stepping motor drive

Stepping motor drive circuit



Criteria for device selection

- -The number of parts can be reduced by using the motor control IC with the built-in output driver.
- -A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- -Suitable for a motor valve drive
 Stepping motor driver for expansion valve 4d
- -Voltage regulator with low current consumption

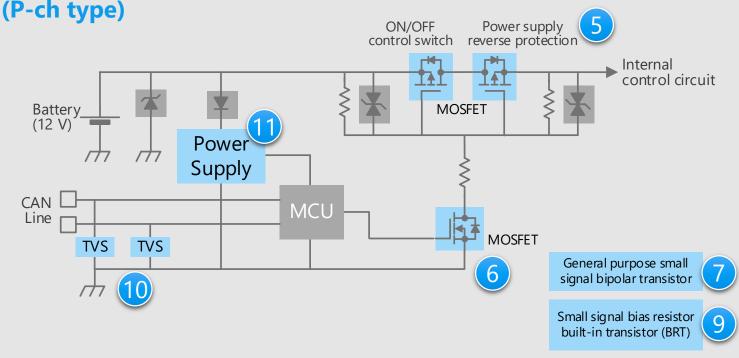
Power supply IC (for MCU)

11

^{*} Click on the numbers in the circuit diagram to jump to the detailed descriptions page

HVAC Detail of switch for power supply ON/OFF control and reverse connection protection (1)

Power supply ON/OFF control and reverse connection protecting circuit



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

-Low on-resistance contributes low power consumption of the system

U-MOS Series -40 V / -60 V P-ch MOSFET

- Extensive product lineup

General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT)

-Suitable for ESD protection TVS diode (for CAN communication)

-Voltage regulator with low current consumption Power supply IC (for MCU)









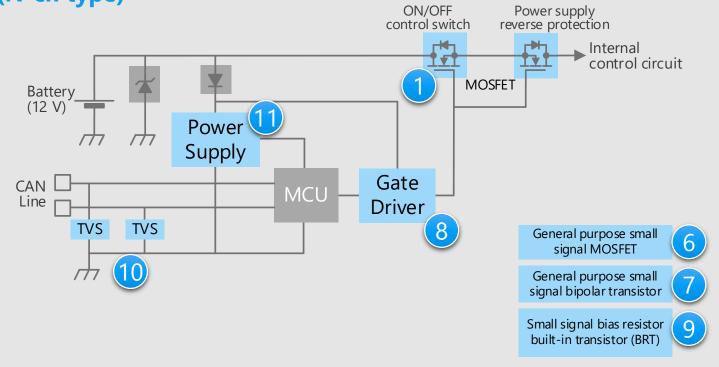




HVAC

Detail of switch for power supply ON/OFF control and reverse connection protection (2)

Power supply ON/OFF control and reverse connection protecting circuit (N-ch type)



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposals from Toshiba

- -Low on-resistance contributes low power consumption of the system U-MOS Series 40 V N-ch MOSFET
- -Gate driver with built-in protection and diagnosis functions Gate driver (for switch)
- Extensive product lineup General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT)
- -Suitable for ESD protection
- -TVS diode (for CAN communication)
- Voltage regulator with low current consumption Power supply IC (for MCU)



















Device solutions to address customer needs

As described above, in the design of HVAC, "Ensuring tolerance to motor lock current. Capable with functional safety", "Reduction of power consumption" and "Miniaturization" are important factors. Toshiba's proposals are based on these three solution perspectives.

Ensuring tolerance to motor lock current.

Capable with functional safety



Reduction of power consumption



Miniaturization



Device solutions to address customer needs

		Robustness	High efficiency • Low loss	Small size package
1	U-MOS Series 40 V N-ch MOSFET			
2	U-MOS Series 100 V N-ch MOSFET			
3	Gate driver (for motor)			
4	Motor driver *			
5	U-MOS Series -40 V / -60 V P-ch MOSFET			
6	General purpose small signal MOSFET			
7	General purpose small signal bipolar transistor			
8	Gate driver (for switch)			
9	Small signal bias resistor built-in transistor (BRT)			
10	TVS diode (for CAN communication)			
11	Power supply IC (for MCU)			

^{*} Damper (LIN communication): TB9056FNG / TB9058FNG, (Direct control type): TB9101FNG / TB9102FNG * Blower: TB9080FG, * Expansion valves in refrigerant cooling system:TB9120AFTG



U-MOS Series 40 V N-ch MOSFET

XPN3R804NC / TK1R4S04PB / TPHR7904PB / TPWR7904PB / TKR74F04PB / TK1R5R04PB







Value provided

The advanced U-MOSIX-H processes enables low on-resistance and low noise, thereby reducing power consumption.

Low loss (reduced on-resistance)

Using low on-resistance technology to contribute to reduced power consumption systems.

On-resistance of 61 % reduction per unit area. (compared to U-MOSIV)

Compact and low loss package

By adopting a Cu connector structure and a double-sided heat dissipation structure, low loss and high heat dissipation are realized.

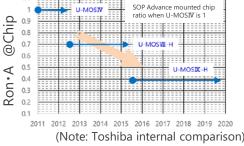
Wettable Frank (WF) package contributes good mountability.

Line un

3 Low noise (low EMI)

Improved chip process reduces surge voltage and ringing time.

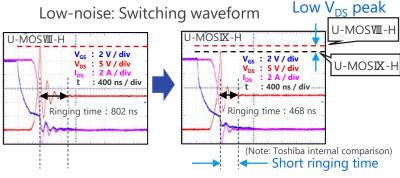
Low Loss: RonA Trend



TO-220SM(W) Cu connector design

Packa reduc comp

Package resistance is reduced by 64 %, compared to D2PAK+.



DSOP Advance(WF)L double-sided cooling package



Thermal resistance is reduced by 76 % @t = 3 s, mounted on board compared to SOP Advance(WF).

יוי	Line up									
- - -	Part number	Drain current	On-resistance (Max) @V _{GS} = 10 V	Package						
_	XPN3R804NC	40 A	3.8 mΩ	TSON Advance(WF)						
	TK1R4S04PB	120 A	1.35 mΩ	DPAK+						
	TPHR7904PB	150 A	0.79 mΩ	SOP Advance(WF)						
	TPWR7904PB	150 A	0.79 mΩ	DSOP Advance(WF)L						
2	TKR74F04PB	250 A	0.74 mΩ	TO-220SM(W)						
_	TK1R5R04PB	160 A	1.5 mΩ	D2PAK+						



U-MOS Series 100 V N-ch MOSFET

Robustness





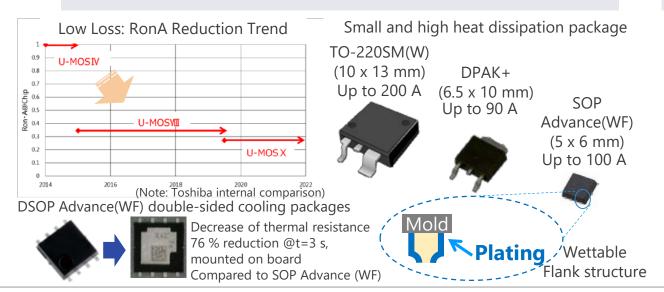
Value provided

Low on-resistance contributes to reduced system power consumption.

XPN2400ANC / TK60S10N1L / XPH4R10ANB / XPW4R10ANB / TK160F10N1L / XK1R9F10QB / XK4R0F10QB

Low loss (reduced on-resistance)

Using low resistance wafer process technology to contribute to reduced power consumption systems.



Small and high heat dissipation package

Small and high heat dissipation packages are realized by adopting a Cu connector structure.

Ensuring mountability by using the Wettable Flank (WF) structure.

Line up			
Part number	Drain current	ON-resistance (Max) @V _{GS} = 10 V	Package
XPN2400ANC *	20 A	23.5 mΩ	TSON Advance(WF)
TK60S10N1L	60 A	6.11 mΩ	DPAK+
XPH4R10ANB	70 A	4.1 mΩ	SOP Advance(WF)
XPW4R10ANB	70 A	4.1 mΩ	DSOP Advance(WF)
TK160F10N1L	160 A	2.4 mΩ	_
XK1R9F10QB	160 A	1.92 mΩ	TO-220SM(W)
XK4R0F10QB *	(60 A)	(4.0 mΩ)	

^{*:} Under Development (The specification is subject to change without notice.)







The high gate drive current capability reduces MOSFET losses and improves the efficiency of system.

High gate drive current

High drive current capability and high speed switching contribute to reduce the loss.

- TPD7211F: ±0.5 A
- TPD7212F, TPD7212FN: -1 / +1.5 A

Built-in protection / diagnostic output function

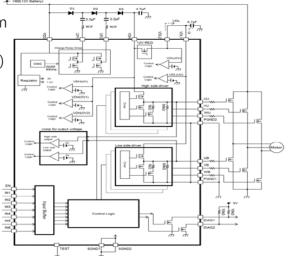
MOSFET is turn off when a signal is input that causes arm short circuit.

Functions to monitor abnormalities of the power supply voltage and output voltage are built-in.

Small surface mount package

PS-8, WQFN32 and SSOP30 are small surface mount packages. It contributes to the miniaturization of system.

Example of application and block diagram of TPD7212F, TPD7212FN (Three phase brushless DC motor control)



Line up					
Part number	TPD7211F	TPD7212F / TPD7212FN			
Function	Half bridge output gate driver Gate driver for three-phase brushless n				
Number of output	t 2 outputs 6 outputs				
Package	PS-8 (2.8 x 2.9 mm)	TPD7212F TPD7212FN Back surface WQFN32 (5 x 5 mm) SSOP30 (7.6 x 10.2 mm			
Features	·For high side P-ch MOSFET drive	· For driving high side N-ch MOSFET			







This is suitable for applications as air conditioner blower motors or battery cooling fans, that required quietness and high efficiency.

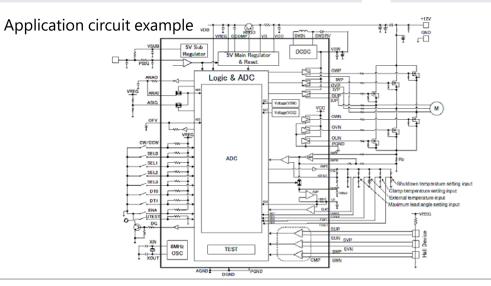
Support two types of rotation control input

The motor speed control is compatible with both PWM signal input and DC voltage input.

No microcontroller required

Since a microcontroller is not required, the area of control board can be reduced and the program development period can be shortened. **3** Various built-in detection functions

Built-in various detection functions such as overcurrent, overtemperature, over voltage, and under voltage.



Line up							
Part number	TB9080FG						
Package	LQFP64-P-1010-0.50E (12 x 12 mm)						
Operating Voltage Range [V]	7 to18						
Sleep consumption current [μΑ, Typ.]	50						
Number of external MOSFETs	N-ch x 6						
Drive control	Sine wave control						







It has built-in output MOSFETs and can drive brushed DC motor directly.

Built-in output MOSFETs

It has built-in output MOSFETs and can drive brushed DC motor directly.

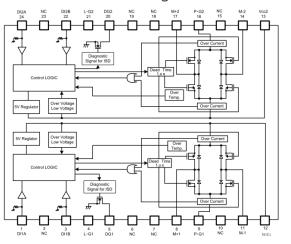
Description Low on-resistance

Low on-resistance contributes to reduce heat generation and power consumption.

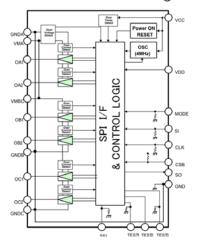
Warious built-in detection functions

Built-in various detection functions such as overcurrent, overtemperature, over voltage, and under voltage.

TB9101FNG block diagram



TB9102FNG block diagram



Line up							
Part number	TB9101FNG	TB9102FNG					
Package	SSOP24-P-300-0.65A (7.6 x 8.3 mm)	September 1					
Power supply voltage [V]	7 to 18	7 to 18					
Output current [A]	±1.0	±1.0					
Allowable power dissipation [W]	1.32	1.32					
On-resistance (High side / Low side) (Typ.) [Ω]	0.6 / 0.6	0.5 / 0.5					
External interface	Direct input	SPI interface					







This is full hardware brushed DC motor driver with LIN communication function.

Simple control by full hardware

No need to develop software. Motor control by LIN communication (slave).

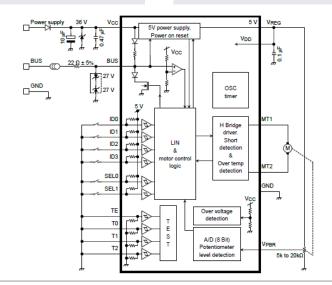
2 Low on-resistance and low standby current

- On-resistance (High Side + Low Side): 2.2 Ω (Typ.)
- Standby current: 10 μA (Max)

Warious built-in detection functions

Built-in various detection functions such as over current, over temperature, over voltage, and under voltage.

TB9056FNG / TB9058FNG block diagram



Line up		
Part number	TB9056FNG	TB9058FNG
Package	SSOP24-P-300-0.65A	September 1
Power supply voltage [V]	7 to 18	7 to 18
Output current [A]	0.3	0.3
Motor drive circuit Type	H-bridge (1ch)	H-bridge (1ch)
On-resistance (High side / Low side) (Typ.) $[\Omega]$	1.0 / 1.2	1.0 / 1.2
Communication Method	LIN rev. 1.3	LIN rev. 1.3 (Enhanced checksum)







Micro stepping drive controlled by single clock input signal only.

Micro stepping drive

- Full step to 1 / 32 step which contributes to reducing noise and vibration is supported.
- Neither high performance MCUs nor software are required. It can be controlled by clock signal.

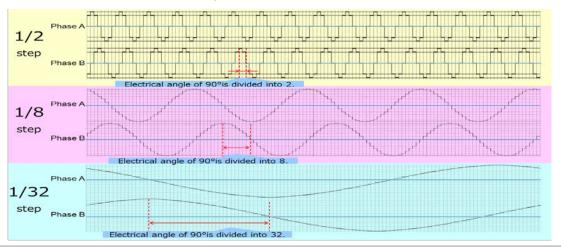
Stall detection

 A detection signal is output, if the IC judges a malrotation.

3 Broad utility

- It can be used for various applications.
- Application example
 Dampers
 Expansion valves
 HUD (Head up display)

Current waveform in micro step



Line up			
Part number	TB9120AFTG		
	P-VQFN28-0606-0.65-002		
Package	6 x 6 mm		
	Wettable frank package contributes good solderbility		
Output device	Built-in MOSFETs for 1 A class		
Output MOSFET	0.0 O (High side + Levy side Type To 25.0C)		
on-resistance	0.8 Ω (High side + Low side, Typ., Ta = 25 °C)		
Detection circuit	Over current, over temp., stall detection and load open		
Standby function	Current consumption less than 10 µA in standby mode Built-in a standby pin		

5

U-MOS Series -40 V / -60 V P-ch MOSFET TJ90S04M3L / TJ60S06M3L / XPH3R114MC / TJ200F04M3L







Value provided

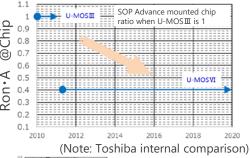
Low on-resistance contributes to reduce system power consumption.

Low loss (reduced on-resistance) and logic level drive

Using low on-resistance technology contributes to reduce system power consumption.

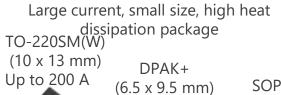
Lineups of logic level drive type are supported.





(Note: To









By 2

Small surface mount package developed

By adopting a Cu connector structure and a double-sided heat dissipation structure, low loss and high heat dissipation are realized.

Wettable Frank (WF) package contributes good mountability.

Line up

Part number	Drain-source Voltage	Drain current	On-resistance (Max) @V _{GS} = -10 V	Package
TJ90S04M3L	-40 V	-90 A	4.3 mΩ	DPAK+
TJ60S06M3L	-60 V	-60 A	11.2 mΩ	DPAK+
XPH3R114MC	-40 V	-100 A	3.1 mΩ	SOP Advance(WF)
TJ200F04M3L	-40 V	-200 A	1.8 mΩ	TO-220SM(W)

◆ Return to Block Diagram TOP

Wettable Flank (WF) structure



General purpose small signal MOSFET SSM3K7002KF / SSM3J168F / SSM3J66MFV







Value provided

Wide lineup of small packages contribute to reduce the size and power consumption of system.

Small package

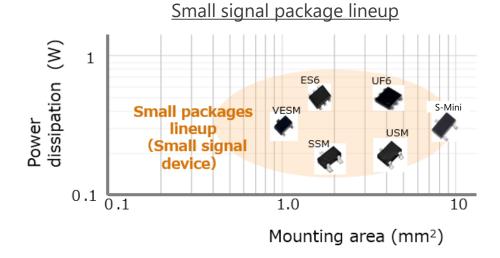
A lineup of various small packages such as SOT-723 (VESM 1.2 x 1.2 mm package) is available, contributing to reduce mounting area.

DescriptionLow voltage drive

SSM3J66MFV can be driven at low gatesource voltage of 1.2 V.

3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Line up							
Part number	Part number		SSM3K7002KF SSM3J168F				
Package V _{DSS} [V]		S-Mini (SOT-346)	S-Mini (SOT-346)	VESM (SOT-723)			
		60	-60	-20			
I _D [A]	I _D [A]		-0.4	-0.8			
R _{DS(ON)}	Тур.	1.2	1.4	0.31			
@ $ V_{GS} = 4.5 V [Ω]$ Max		1.75	1.9	0.39			
Drive voltage [V]		4.5	-4.0	-1.2			
Polarity		N-ch	P-ch	P-ch			



General purpose small signal bipolar transistor 25C2712 / 25A1162 / 25C4116 / 25A1586 / TTA501 / TTC501 and others







Value provided

Extensive product lineup to meet customers' needs.

Extensive lineup of packages

Various packages such as 1-in-1, 2-in-1 are provided and suitable products for circuit board design are selectable.

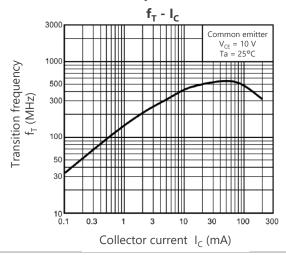
Extensive product lineup

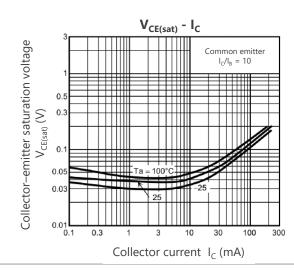
Various product lineups, such as general purpose, low noise, low $V_{\text{CE(sat)}}$ and high current types are provided. Products can be selected in accordance to the application.

3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

Characteristic examples of 2SC2712





Line up								
Package		SOT-23F		USM (SOT-323) UFM (SOT-323F)*		S-Mini (SOT-346)		
Classification	V _{CEO} [V]	I _C [mA]	NPN	PNP	NPN	PNP	NPN	PNP
Conoral nurnoso	50	150			2SC4116	2SA1586	2SC2712	2SA1162
General purpose	50	500					2SC3325	2SA1313
Low noise	120	100			2SC4117	2SA1587	2SC2713	2SA1163
	50	1700				2SA2195*		
High current	50	2000		TTA501				
	100	2500	TTC501					







A charge pump circuit for the N-channel MOSFET gate drive is built in, allowing for easy semiconductor relay configuration.

Built-in charge pump circuit

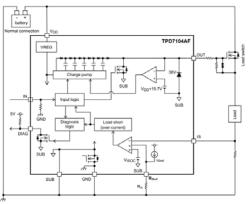
Built-in charge pump circuit enables N-channel MOSFET as high side switch. Easy to configure a semiconductor relay. **Can be controlled by logic** level voltage

It is possible that Direct control by output signal of MCUs or CMOS logic ICs.

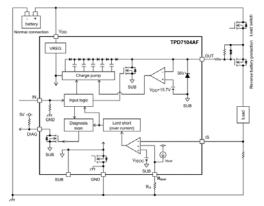
3 Small package

The small surface mount packages such as PS-8, SSOP16 and WSON10A contribute to the miniaturization of equipment.

Semiconductor relay (switch) application (TPD7104AF)



Power supply reverse connection protection MOSFET control (TPD7104AF)



Back to back configuration

Line up								
Part number	TPD7104AF	TPD7106F	TPD7107F					
Package	PS-8 (2.8 x 2.9 mm)	SSOP16 (5.5 x 6.4 mm)	WSON10A (3 x 3 mm)					
Features	Operating power supply voltage range: 5 to 18 V Built-in power supply reverse connection protection function (Supported for power supply reverse connection protection MOSFET applications)	Operating power supply voltage range: 4.5 to 27 V Built-in power supply reverse connection protection function (Supported for power supply reverse connection protection MOSFET applications)	Operating power supply voltage range: 5.75 to 26 V Current sense output Protective functions; overcurrent, overtemperature, GND disconnect, etc. reverse battery connection Diagnosis output; overcurrent, load open, overtemperature, etc.					



Small signal bias resistor built-in transistor (BRT) RN1907FE / RN2907FE / RN1901 / RN2901 Series







Value provided

Extensive product lineup to meet customers' needs.

Built-in bias resistor type
(BRT: Bias Resistor built-in Transistor)

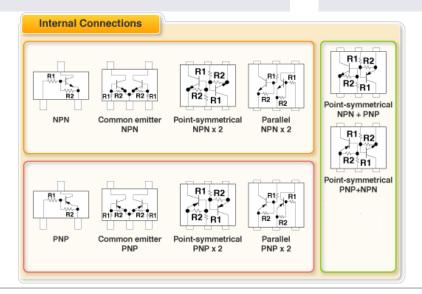
The BRTs contribute to reduction of the number of components, assembly workload and mounting area of circuit boards.

2 Extensive lineup of package and pin assignment

Various package lineups, such as 1-in-1, 2-in-1 and various pin assignment type are provided and suitable products for circuit board design are selectable.

3 AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Line up				
Part number		NPN (BRT)	PNP (BRT)	
Package	ES6 (SOT-563)	RN1907FE	RN2907FE	
	US6 (SOT-363)	RN1901	RN2901	
V _{CEO} (Max) [V]		50	-50	
I _C [mA]		100	-100	







TVS diodes prevent system damage and malfunction caused by electrostatic discharge (ESD).

Improve ESD pulse absorbability

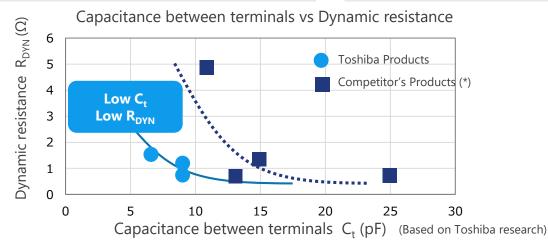
Toshiba proprietary Zener process improves the ESD pulse absorption of TVS diodes. (Both low dynamic resistance R_{DYN} and low capacitance between terminals C_{t})

Supports CAN, CAN FD and FlexRay

These are products applicable to invehicle LAN communication such as CAN, CAN FD and FlexRay.

3 High ESD immunity

 $V_{ESD} > \pm 30 \text{ kV} @ ISO 10605$ $V_{ESD} > \pm 20 \text{ kV} (L4) @ IEC61000-4-2$



Line up					
Part number	DF3D18FU	DF3D29FU	DF3D36FU		
Package	USM (SOT-323)				
V _{ESD} [kV] @ISO 10605	±30	±30	±20		
V _{RWM} (Max) [V]	12	24	28		
C _t (Typ. / Max) [pF]	9 / 10		6.5 / 8		
R _{DYN} (Typ.) [Ω]	0.8	1.1	1.5		

(NOTE): This product is an ESD protection diode and cannot be used for purposes other than ESD protection.

(*): Measurements of the commercial product







This is voltage regulator with low current consumption, and various monitoring functions such as WDT^[Note] contribute to improving system stability.

Low current consumption

External transistor type voltage regulator with low current consumption.

Load stability is +/-1 %.

2 Built-in WDT and various monitoring functions

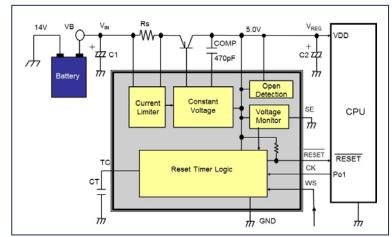
The WDT monitors the operation of the MCU.

In addition, current detection functions contribute to improving system safety.

3 AEC-Q100 qualified

It is AEC-Q100 qualified and can be used for various automotive applications.

Application circuit example (The current limiter can be adjusted by an external resistor.)



Line up				
	Part number	TB9005FNG		
	Package	SSOP20 (6.4 x 7.0 mm		
Curren	t consumption I _{CC} (Typ.) [μΑ]	90 (@V _{IN} = 12 V, Ta = 25 °C)		
Load	stability VLOAD (Max) [%]	1 (@ILOAD = 1 to 300 mA)		
u C	Number of outputs	1 ch (5 V)		
Function	Circuit type	External transistor type		
	WDT, Overcurrent limitation	✓		

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